

January 1989

PRAM Four Channel Programmable Operational Amplifier

Features

- This Circuit is Processed in Accordance to Mil-Std-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- Digital Programmability
- High Slew Rate (Uncompensated) 20V/ μ s Min
(Compensated) 6V/ μ s Min
- Wide Gain Bandwidth
(Uncompensated) 20MHz Min
(Compensated) 4MHz Min
- High Gain 50kV/V Min
- Low Offset Current 50nA Max
- Single Capacitor Compensation For Unity Gain
- DTL/TTL Compatible Inputs

Applications

- Single Selection/Multiplexing
- Op Amp Gain Stage
- Frequency Oscillator
- Filter Characteristics
- Add-Subtract Functions
- Integrator Characteristics
- Comparator Levels

Description

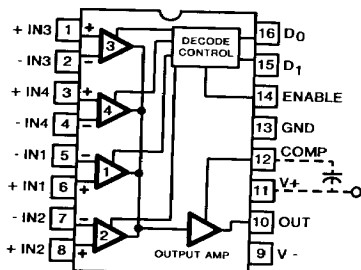
The HA-2400/883 is a four channel programmable amplifier providing a level of versatility unsurpassed by any other monolithic operational amplifier. Versatility is achieved by employing four input amplifier channels, any one (or none) of which may be electronically selected and connected to a single output stage through DTL/TTL compatible address inputs. The device formed by the output and the selected pair of inputs is an op amp which delivers excellent slew rate, gain bandwidth and power bandwidth performance. Other advantages features for these dielectrically isolated amplifiers include high voltage gain and input impedance coupled with low input offset voltage and offset current. External compensation is not required on this device at closed loop gains greater than 10.

Each channel of the HA-2400/883 can be controlled and operated with suitable feedback networks in any of the standard op amp configurations. This specialization makes these amplifiers excellent components for multiplexing, signal selection, and mathematical function designs. With 20V/ μ s slew rate, 20MHz gain bandwidth, and low input bias currents makes these devices ideal building blocks for signal generators, active filters, and data acquisition designs. Programmability coupled with 9mV maximum offset voltage and 50nA offset current makes these amplifiers outstanding components for the signal conditioning circuits.

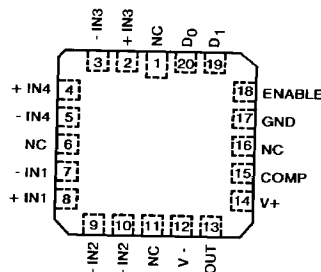
The HA-2400/883 is available in the 16 pin Dual-in-Line Ceramic package and a 20 pin LCC package. The HA-2400/883 is specified from -55°C to +125°C.

Pinouts

HA1-2400/883 (CERAMIC DIP)
TOP VIEW



HA4-2400/883 (CERAMIC LCC)
TOP VIEW



TRUTH TABLE

D ₁	D ₀	EN	SELECTED CHANNEL
L	L	H	1
L	H	H	2
H	L	H	3
H	H	H	4
X	X	L	NONE

Absolute Maximum Ratings

Voltage Between V+ and V- Terminals	45V
Differential Input Voltage	$\pm V_{SUPPLY}$
Voltage at Either Input Terminal	V+ to V-
Digital Input Voltage	-0.76V to +10V
Peak Output Current (Short Circuit Protected)	$I_{SC} < \pm 33mA$
Junction Temperature (T_J)	+175°C
Storage Temperature Range	-65°C to +150°C
ESD Rating	<2000V
Lead Temperature (Soldering 10 sec)	+275°C

CAUTION: Absolute maximum ratings are limiting values, applied individually beyond which the serviceability of the circuit may be impaired. Functional operability under any of these conditions is not necessarily implied.

Thermal Information

Thermal Resistance	θ_{JA}	θ_{JC}
Ceramic DIP Package	91°C/W	25°C/W
Ceramic LCC Package	88°C/W	28°C/W
Internal Power Dissipation		
Package Power Dissipation Limit at +75°C for $T_J \leq +175^\circ C$		
Ceramic DIP Package	1.11W	
Ceramic LCC Package	1.14W	
Package Power Dissipation Derating Factor Above +75°C		
Ceramic DIP Package	11.1mW/°C	
Ceramic LCC Package	11.4mW/°C	

Recommended Operating Conditions

Operating Temperature Range	-55°C to +125°C	Negative Supply Voltage	-15V
Operating Supply Voltage	+15V		

TABLE 1. D.C. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: V+ = +15V, V- = -15V, $R_S = 100\Omega$, $R_L = 500k\Omega$, $V_O = 0V$ Unless Otherwise Specified.
Digital Inputs: $V_{IL} = +0.5V$, $V_{IH} = +2.4V$, Limits Apply to Each of the Four Channels, When Addressed.

D.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Offset Voltage	V_{IO}	$V_{CM} = 0V$	1	+25°C	-9	9	mV
			2, 3	+125°C, -55°C	-11	11	mV
Input Bias Current	$+I_B$	$V_{CM} = 0V$ $+R_S = 100k\Omega$ $-R_S = 100\Omega$	1	+25°C	-200	200	nA
			2, 3	+125°C, -55°C	-400	400	nA
	$-I_B$	$V_{CM} = 0V$ $+R_S = 100\Omega$ $-R_S = 100k\Omega$	1	+25°C	-200	200	nA
			2, 3	+125°C, -55°C	-400	400	nA
Input Offset Current	I_{IO}	$V_{CM} = 0V$ $+R_S = 100k\Omega$ $-R_S = 100k\Omega$	1	+25°C	-50	50	nA
			2, 3	+125°C, -55°C	-100	100	nA
Common Mode Range	+CMR	V+ = +6V V- = -24V $V_{OUT} = -9V$	1	+25°C	9	-	V
			2, 3	+125°C, -55°C	9	-	V
	-CMR	V+ = +24V V- = -6V $V_{OUT} = +9V$	1	+25°C	-	-9	V
			2, 3	+125°C, -55°C	-	-9	V
Large Signal Voltage Gain	A_V	$V_{OUT} = -10V$ to $+10V$ $R_L = 2k\Omega$	4	+25°C	50	-	kV/V
			5, 6	+125°C, -55°C	25	-	kV/V
Common Mode Rejection Ratio	+CMRR	$\Delta V_{CM} = +5V$ $+V = +10V$ $-V = -20V$ $V_{OUT} = -5V$	1	+25°C	80	-	dB
			2, 3	+125°C, -55°C	80	-	dB
	-CMRR	$\Delta V_{CM} = -5V$ $+V = +20V$ $-V = -10V$ $V_{OUT} = +5V$	1	+25°C	80	-	dB
			2, 3	+125°C, -55°C	80	-	dB
Output Voltage Swing	$+V_{OUT}$	$R_L = 2k\Omega$	4	+25°C	+10	-	V
			5, 6	+125°C, -55°C	+10	-	V
	$-V_{OUT}$	$R_L = 2k\Omega$	4	+25°C	-	-10	V
			5, 6	+125°C, -55°C	-	-10	V

CAUTION: This device is sensitive to electrostatic discharge. Proper I.C. handling procedures should be followed.

TABLE 1. D.C. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_+ = +15V$, $V_- = -15V$, $R_S = 100\Omega$, $R_L = 500k\Omega$, $V_O = 0V$ Unless Otherwise Specified.
Digital Inputs: $V_{IL} = +0.5V$, $V_{IH} = +2.4V$, Limits Apply to Each of the Four Channels, When Addressed

PARAMETER	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Output Current	$+I_{OUT}$	$V_{OUT} = +10V$	4	$+25^\circ C$	+10	-	mA
	$-I_{OUT}$	$V_{OUT} = -10V$	4	$+25^\circ C$	-	-10	mA
Supply Current	$+I_{CC}$	$V_{OUT} = 0V$	1	$+25^\circ C$	-	6	mA
			2, 3	$+125^\circ C, -55^\circ C$	-	7	mA
	$-I_{CC}$	$V_{OUT} = 0V$	1	$+25^\circ C$	-6	-	mA
			2, 3	$+125^\circ C, -55^\circ C$	-7	-	mA
Power Supply Rejection Ratio	+PSRR	$\Delta V_{SUP} = \pm 5V$ $V_+ = +20V, V_- = -15V$ $V_+ = +10V, V_- = -15V$	1	$+25^\circ C$	74	-	dB
			2, 3	$+125^\circ C, -55^\circ C$	74	-	dB
	-PSRR	$\Delta V_{SUP} = \pm 5V$ $V_+ = +15V, V_- = -20V$ $V_+ = +15V, V_- = -10V$	1	$+25^\circ C$	74	-	dB
			2, 3	$+125^\circ C, -55^\circ C$	74	-	dB
Crosstalk	C_T	$V_{IN} = \pm 10V$	1	$+25^\circ C$	-80	-	dB
Digital Logic Current	I_{IL}	$V_{IL} = 0V$	1	$+25^\circ C$	-	1.5	mA
			2, 3	$+125^\circ C, -55^\circ C$	-	1.5	mA
	I_{IH}	$V_{IH} = 5.0V$	1	$+25^\circ C$	-	1	μA
			2, 3	$+125^\circ C, -55^\circ C$	-	1	μA

TABLE 2. A.C. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $V_+ = +15V$, $V_- = -15V$, $R_L = 2k\Omega$, $C_{LOAD} = 50pF$, Unless Otherwise Specified.
Subscript 1 Refers to $A_V = +1$, $C_{COMP} = 15pF$
Digital Inputs: $V_{IL} = +0.5V$, $V_{IH} = +2.4V$, Limits Apply to Each of the Four Channels, When Addressed.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Slew Rate ₁	$+SR_1$	$V_{OUT} = -5V$ to $+5V$	7	$+25^\circ C$	6	-	$V/\mu s$
	$-SR_1$	$V_{OUT} = +5V$ to $-5V$	7	$+25^\circ C$	6	-	$V/\mu s$
Rise & Fall Time	TR_1	$V_{OUT} = 0$ to $+200mV$	7	$+25^\circ C$	-	45	ns
	TF_1	$V_{OUT} = 0$ to $-200mV$	7	$+25^\circ C$	-	45	ns
Overshoot	$+OS_1$	$V_{OUT} = 0$ to $+200mV$	7	$+25^\circ C$	-	40	%
	$-OS_1$	$V_{OUT} = 0$ to $-200mV$	7	$+25^\circ C$	-	40	%

CAUTION: This device is sensitive to electrostatic discharge. Proper I.C. handling procedures should be followed.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: $V_+ = +15V$, $V_- = -15V$, Unless Otherwise Specified.
Subscript 2 Refers to $A_V = +10$, $C_{COMP} = 0pF$

PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Unity Gain Bandwidth	UGBW ₁	$A_V = +1$, $C_{COMP} = 15pF$ $R_L = 2k\Omega$, $C_L = 50pF$	1	+25°C	4	-	MHz
Gain Bandwidth Product	GBWP ₂	$A_V = +10$, $C_{COMP} = 0pF$ $R_L = 2k\Omega$, $C_L = 50pF$	1	+25°C	20	-	MHz
Full Power Bandwidth ₁	FPBW ₁	$R_L = 2k\Omega$, $A_V = +1V$, $V_O = \pm 10V$, $C_L = 50pF$, $C_{COMP} = 15pF$	1, 2	+25°C	95	-	kHz
Full Power Bandwidth ₂	FPBW ₂	$R_L = 2k\Omega$, $A_V = +10V$, $V_O = \pm 10V$, $C_L = 50pF$, $C_{COMP} = 0pF$	1, 2	+25°C	300	-	kHz
Settling Time	TSET1	$A_V = +1$, $C_{COMP} = 15pF$ $R_L = 2k\Omega$, $C_L = 50pF$, $V_O = 10V_{p-p}$ to 0.1% F.V. Logic Control = +5.0V	1	+25°C	-	2.5	μs
Slew Rate ₂	+SR ₂	$V_{OUT} = -5V$ to $+5V$ $R_L = 2k\Omega$, $C_L = 50pF$, $A_V = +10$, $C_{COMP} = 0pF$	1	+25°C	20	-	V/ μs
	-SR ₂	$V_{OUT} = +5V$ to $-5V$ $R_L = 2k\Omega$, $C_L = 50pF$, $A_V = +10$, $C_{COMP} = 0pF$	1	+25°C	20	-	V/ μs
Output Delay	TDEL	$R_L = 2k\Omega$, $C_L = 50pF$, $C_{COMP} = 15pF$, $V_{IN} = +5V$	1	+25°C	-	250	ns
Minimum Closed Loop Stability	CLS ₁	$R_L = 2k\Omega$, $C_L = 50pF$, $C_{COMP} = 15pF$	1	+25°C	1	-	V/V
	CLS ₂	$R_L = 2k\Omega$, $C_L = 50pF$, $C_{COMP} = 0pF$	1	+25°C	10	-	V/V

NOTES: 1. The parameters listed in this table are controlled via design or process parameters and are not directly tested at final production. These parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot to lot and within lot variation.

2. $FPBW = \frac{S.R.}{2\pi V_{peak}}$

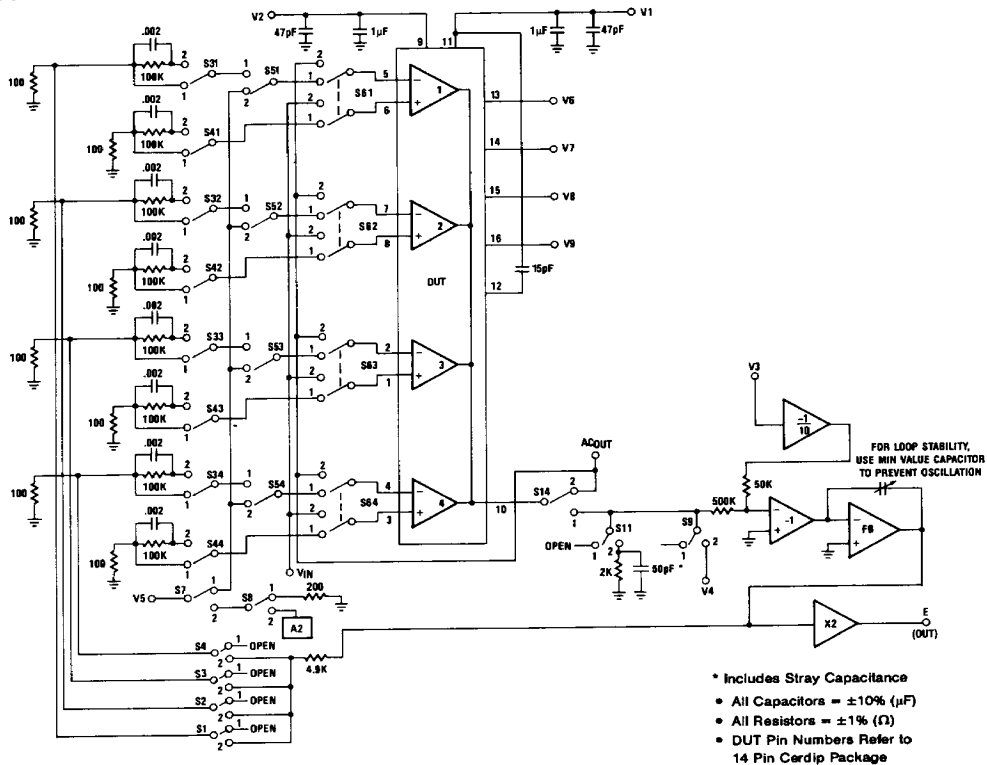
TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLES 1 & 2)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1*, 2, 3, 4, 5, 6, 7
Group A Test Requirements	1, 2, 3, 4, 5, 6, 7
Groups C & D Endpoints	1

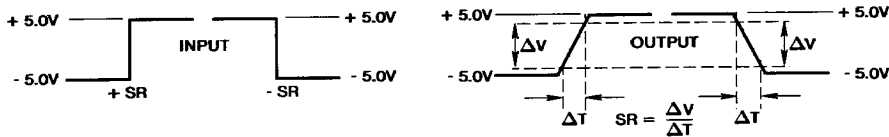
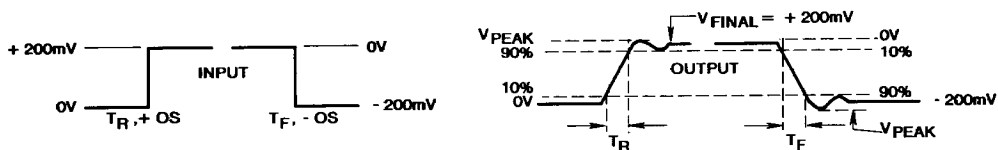
* PDA applies to Subgroup 1 only.

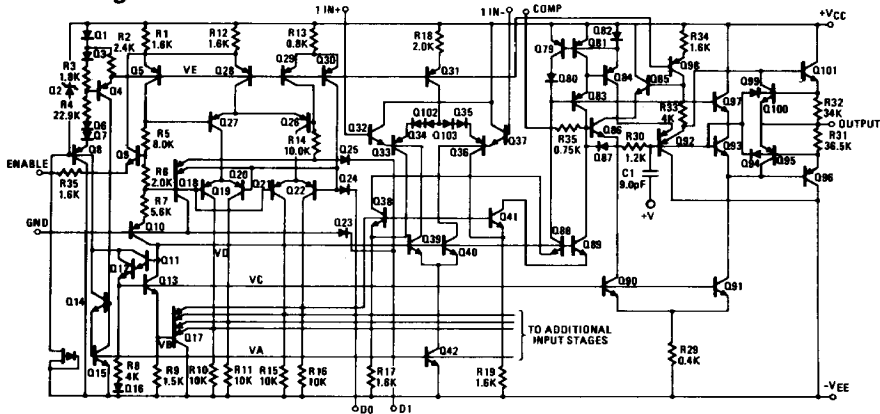
The subgroup assignments of the parameters in these tables were patterned after DESC SMD #5962-87783.

CAUTION: This device is sensitive to electrostatic discharge. Proper I.C. handling procedures should be followed.

Test Circuit

For Detailed Information, Refer to HA-2400/883 Test Tech Brief

Test Waveforms**SLEW RATE WAVEFORMS****OVERSHOOT, RISE & FALL TIME WAVEFORMS**

Schematic Diagram**Die Characteristics****DIE DIMENSIONS:**

88 x 67 x 19 mils
(2240 x 1710 x 483 μ m)

METALLIZATION:

Type: Aluminum
Thickness: 16k $\text{\AA}$ $\pm$ 2k $\text{\AA}$

GLASSIVATION:

Type: Nitride
Thickness: 7k $\text{\AA}$ $\pm$ 0.7k $\text{\AA}$

SUBSTRATE POTENTIAL (POWERED UP): Unbiased

DIE ATTACH:

Material: Gold/Silicon Eutectic Alloy
Temperature: Ceramic DIP — 460 $^{\circ}$ C (Max)
Ceramic LCC — 420 $^{\circ}$ C (Max)

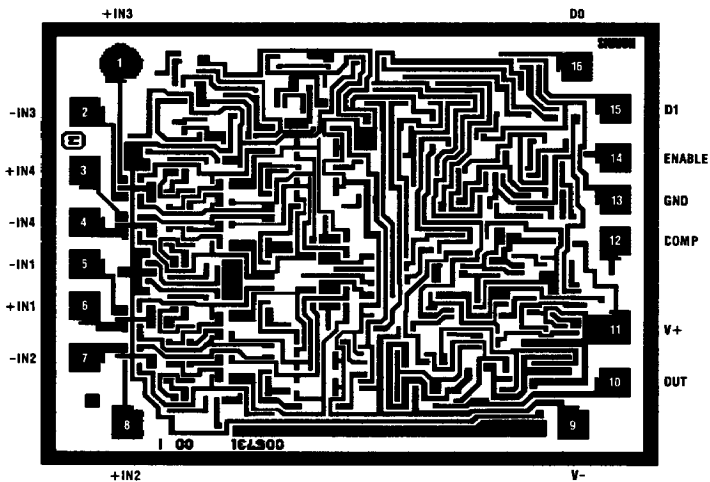
WORST CASE CURRENT DENSITY:

0.7 x 10⁵A/cm²

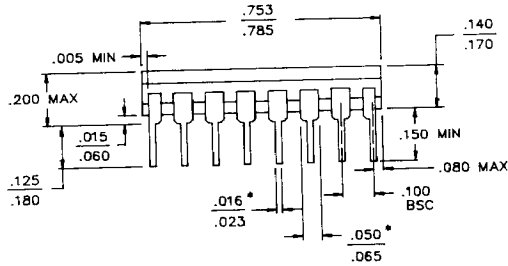
ACTIVE DEVICE COUNT: 251

Metallization Mask Layout

HA-2400/883



NOTE: Pin Numbers Correspond to DIP Package Only.

Packaging[†]**16 PIN CERAMIC DIP**

* INCREASE MAX LIMIT BY .003 INCHES
MEASURED AT CENTER OF FLAT FOR
SOLDER FINISH

LEAD MATERIAL: Type B

LEAD FINISH: Type A

PACKAGE MATERIAL: Ceramic, 90% Alumina

PACKAGE SEAL:

Material: Glass Frit

Temperature: 450°C ± 10°C

Method: Furnace Seal

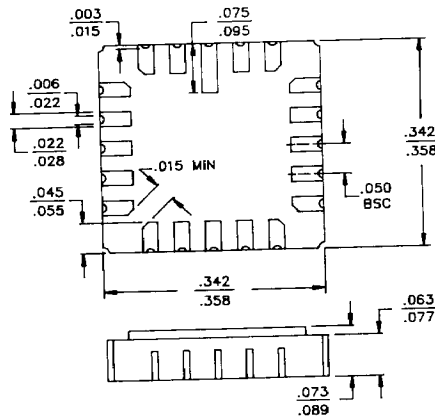
INTERNAL LEAD WIRE:

Material: Aluminum

Diameter: 1.25 Mil

Bonding Method: Ultrasonic

COMPLIANT OUTLINE: 38510 D-2

20 PAD CERAMIC LCC

PAD MATERIAL: Type C

PAD FINISH: Type A

FINISH DIMENSION: Type A

PACKAGE MATERIAL: Multilayer Ceramic, 90% Alumina

PACKAGE SEAL:

Material: Gold/Tin (80/20)

Temperature: 320°C ± 10°C

Method: Furnace Braze

INTERNAL LEAD WIRE:

Material: Aluminum

Diameter: 1.25 Mil

Bonding Method: Ultrasonic

COMPLIANT OUTLINE: 38510 C-2

NOTE: All Dimensions are $\frac{\text{Min}}{\text{Max}}$, Dimensions are in inches.

[†]Mil-M-38510 Compliant Materials, Finishes, and Dimensions.